

< HIGH VOLTAGE DIODE MODULES >

RM1500DG-90X

HIGH POWER SWITCHING USE
INSULATED TYPE

High Voltage Diode Modules

RM1500DG-90X



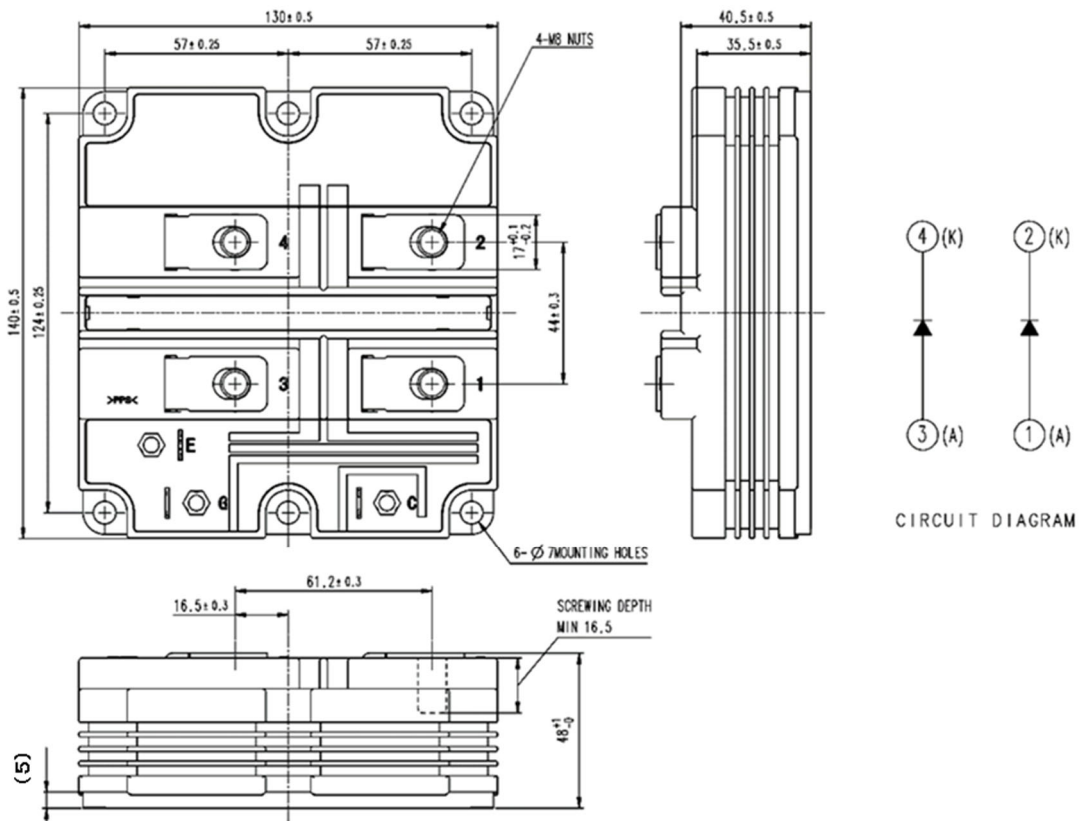
- I_F2 x 1500A
- V_{RRM}4500V
- 2-element in a Pack
- High Insulated Type
- RFC Diode
- AISiC Baseplate

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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MAXIMUM RATINGS

Symbol	Item	Conditions	Ratings	Unit
V _{RRM}	Repetitive peak reverse voltage	V _{GE} = 0 V, T _j = -40...+150 °C	4500	V
		V _{GE} = 0 V, T _j = -50 °C	4400	
I _F	Forward current (note1)	DC, T _c = 70°C	1500	A
I _{FSM}	Surge (non-repetitive) forward current	T _{j_start} = 150°C, t _p = 10 ms, Half-sine wave, V _R = 0 V	12.4	kA
I _t ²	Surge current load integral		768	kA ² s
P _{tot}	Maximum power dissipation	T _c = 25°C	8800	W
V _{iso}	Isolation voltage	RMS, sinusoidal, f = 60 Hz, t = 1 min.	10200	V
V _e	Partial discharge extinction voltage	RMS, sinusoidal, f = 60 Hz, Q _{PD} ≤ 10 pC	5100	V
T _j	Junction temperature		-50 ~ +150	°C
T _{top}	Operating junction temperature		-50 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min	Typ	Max		
I _{RRM}	Repetitive reverse current	V _{RM} = V _{RRM}	T _j = 25°C	—	—	2.5	mA
			T _j = 125°C	—	2.5	—	
			T _j = 150°C	—	—	40.0	
V _{FM} (Terminal)	Forward voltage	I _F = 1500 A	T _j = 25°C	—	3.05	—	V
			T _j = 125°C	—	3.75	—	
			T _j = 150°C	—	3.90	—	
V _{FM} (Chip)	Forward voltage	I _F = 1500 A	T _j = 25°C	—	2.50	—	V
			T _j = 125°C	—	3.10	—	
			T _j = 150°C	—	3.20	3.70	
t _{rr}	Reverse recovery time		T _j = 125°C	—	1.60	—	μs
			T _j = 150°C	—	1.85	—	
I _{rr}	Reverse recovery current	V _{CC} = 2800 V I _F = 1500 A	T _j = 125°C	—	1800	—	A
			T _j = 150°C	—	1800	—	
Q _{rr(10%)}	Reverse recovery charge (Note 2)	-d _{IF} /d _t ≅	T _j = 125°C	—	2640	—	μC
			T _j = 150°C	—	2690	—	
Q _{rr}	Reverse recovery charge	4500 A/μs @ T _j = 25°C 4200 A/μs @ T _j = 125°C 4050 A/μs @ T _j = 150°C	T _j = 125°C	—	2850	—	μC
			T _j = 150°C	—	2900	—	
			T _j = 25°C	—	3.75	—	
E _{rec(10%)}	Reverse recovery energy (Note 3) per pulse	L _s = 150 nH	T _j = 125°C	—	4.75	—	J
			T _j = 150°C	—	4.85	—	
			T _j = 25°C	—	3.90	—	
E _{rec}	Reverse recovery energy per pulse	Inductive load	T _j = 125°C	—	5.25	—	J
			T _j = 150°C	—	5.40	—	
			T _j = 25°C	—	3.90	—	

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THERMAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
$R_{th(j-c)}$	Thermal resistance	Junction to Case (per 1/2 module)	—	—	14.2	K/kW
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, $\lambda_{grease} = 1 \text{ W/m}^2\text{K}$ $D_{(c-s)} = 80 \mu\text{m}$ (per 1/2 module)	—	15.0	—	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
M_t	Mounting torque	M8 : Main terminals screw	7.0	—	19.0	N·m
M_s		M6 : Mounting screw	3.0	—	6.0	N·m
m	Mass		—	1.0	—	kg
CTI	Comparative tracking index		600	—	—	—
d_a	Clearance		26.0	—	—	mm
d_s	Creepage distance		56.0	—	—	mm
L_{PAK}	Parasitic stray inductance	1/2 module	—	41	—	nH
R_{AA+KK}	Internal lead resistance	$T_c = 25^\circ\text{C}$, 1/2 module	—	0.36	—	mΩ

Note 1. The possible running current is 1200Arms.

Note 2. $Q_{rr(10\%)}$ is the integral of $I_{rr} \times dt$ ($t(0A|F)-t(-0.1I_F)$)

Note 3. $E_{rec(10\%)}$ is the integral of $0.1V_R \times 0.1I_F \times dt$.

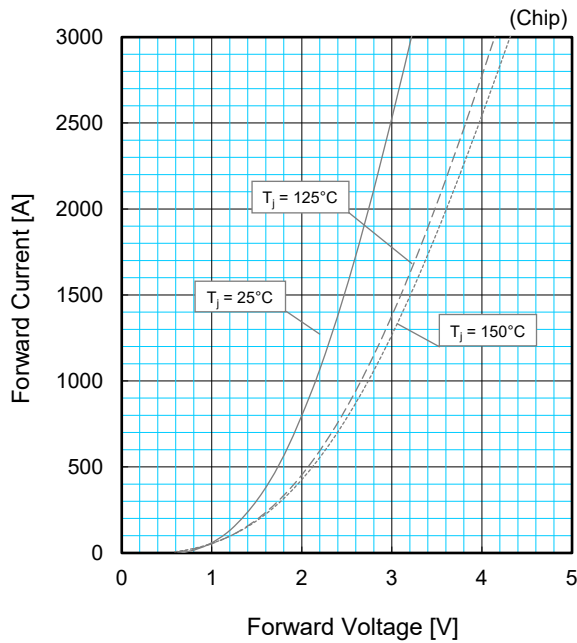
Note 4. Definition of all item is according to IEC 60747, unless otherwise specified.

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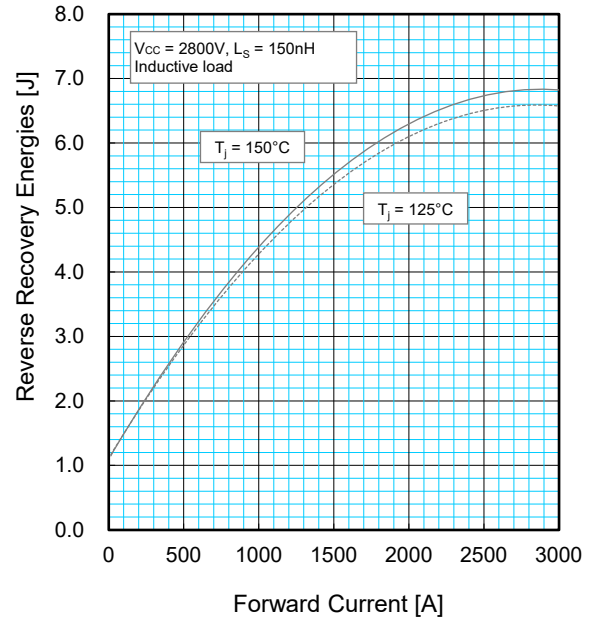
HIGH POWER SWITCHING USE
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PERFORMANCE CURVES

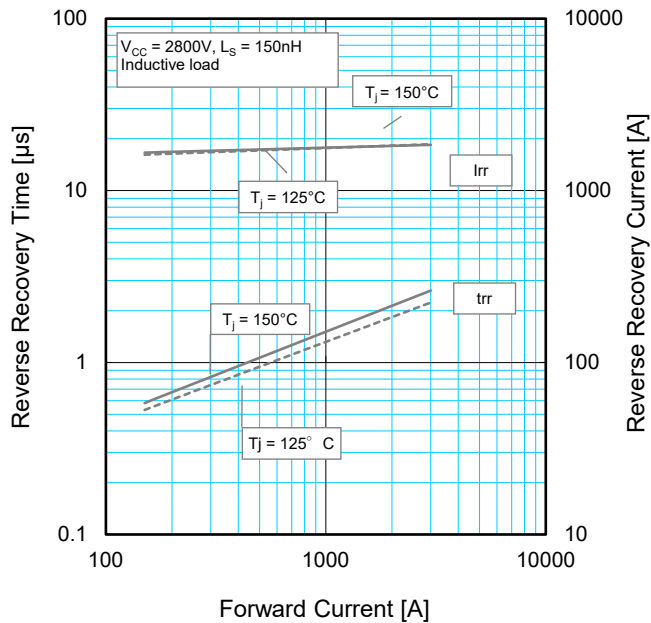
FORWARD CHARACTERISTICS (TYPICAL)



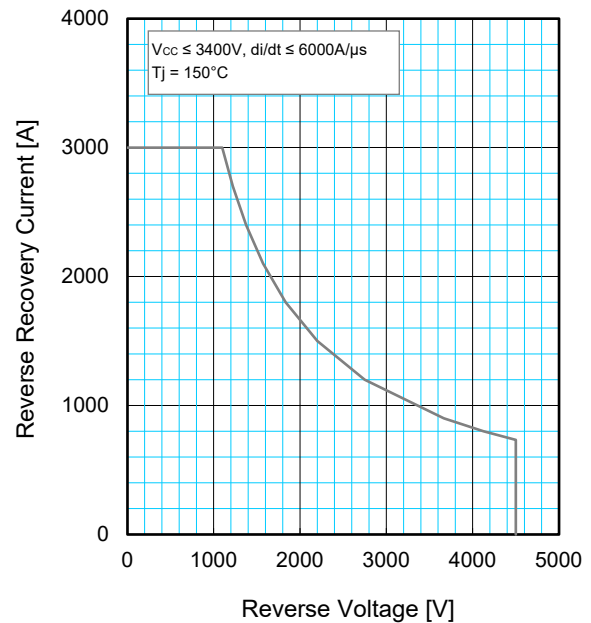
REVERSE RECOVERY ENERGY CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

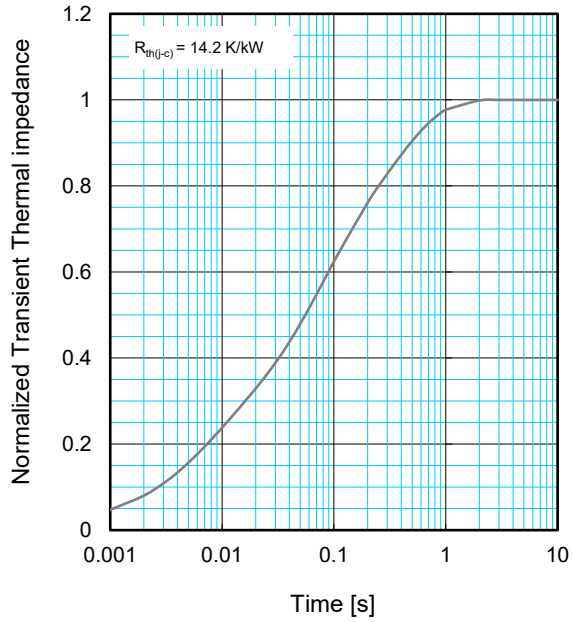


REVERSE RECOVERY SAFE OPERATING AREA (RRSOA)



PERFORMANCE CURVES

TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

	1	2	3	4
$R_i / R_{th(j-c)}$:	0.0096	0.1893	0.4044	0.3967
τ_i [sec]:	0.0001	0.0058	0.0602	0.3512

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